

	Typ	L #	Hits	Search T xt	DBs	Tim Stamp
1	BRS	L1	273	single near4 plasma near4 etching	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/29 15:43
2	BRS	L2	13	1 with ("hard mask" or "silicon nitride" or "silicon oxynitride" or SiN or SiON)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/29 15:44

	Type	L #	Hits	Search Text	DBs
1	BRS	L5	1	(etch\$4 or strip\$4) near8 sacrifial near8 "hard mask"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L6	6002	(etch\$4 or strip\$4 or remov\$4) near8 (sacrifial or resist or photoresist or BARC) near8 ("hard mask" or "silicon nitride" or "silicon oxynitride" or SiN or SiON)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L7	4854	(etch\$4 or strip\$4 or remov\$4) near8 (sacrifial or resist or photoresist or BARC) near8 ("hard mask" or "silicon nitride" or "silicon oxynitride" or SiN or SiON)	USPAT; US-PGP UB
4	BRS	L8	1087	7 same plasma	USPAT; US-PGP UB